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# 4AJ11

Silicon P-Channel Power MOS FET Array

# HITACHI

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## Application

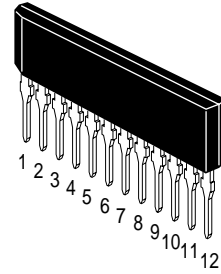
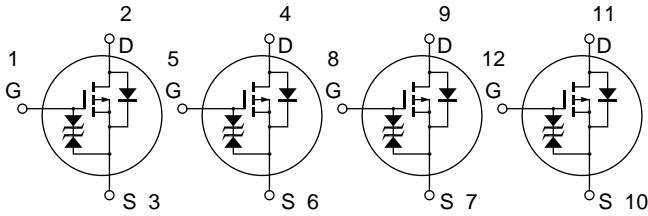
High speed power switching

## Features

- Low on-resistance  
 $R_{DS(on)} = 0.13 \Omega, V_{GS} = -10 \text{ V}, I_D = -4 \text{ A}$   
 $R_{DS(on)} = 0.17 \Omega, V_{GS} = -4 \text{ V}, I_D = -4 \text{ A}$
- Capable of 4 V gate drive
- Low drive current
- High speed switching
- High density mounting
- Suitable for motor driver and solenoid driver and lamp driver

## Outline

SP-12



1, 5, 8, 12. Gate  
2, 4, 9, 11. Drain  
3, 6, 7, 10. Source

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-8	A
Drain peak current	$I_{D(pulse)}^{*1}$	-32	A
Body to drain diode reverse drain current	$I_{DR}$	-8	A
Channel dissipation	$P_{ch} (T_c = 25^\circ C)^{*2}$	28	W
Channel dissipation	$P_{ch}^{*2}$	4	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

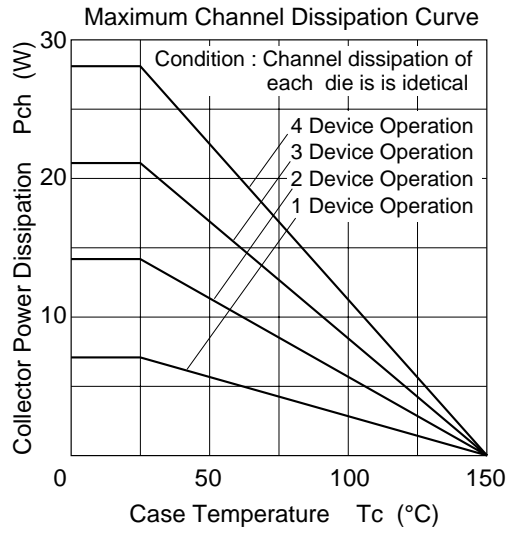
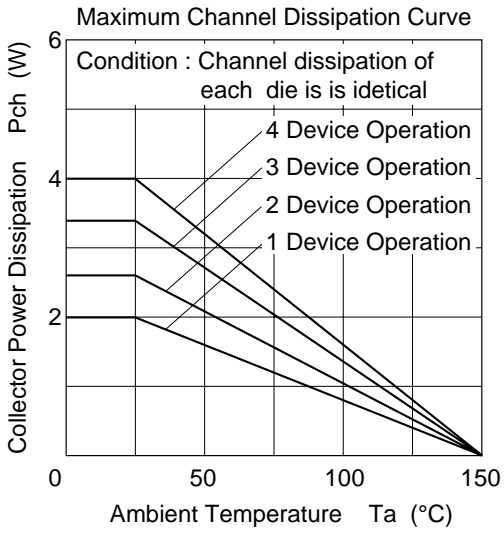
Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$

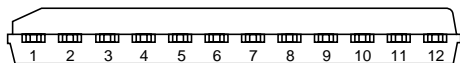
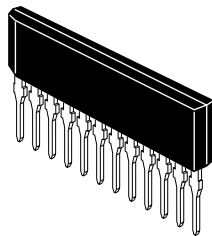
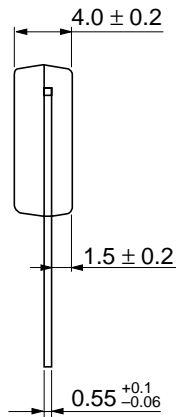
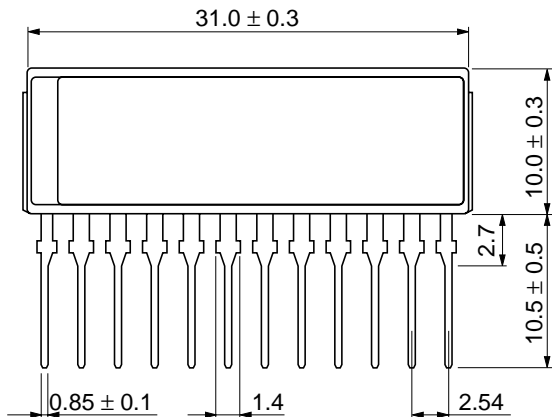
2. 4 Devices operation

## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-250	$\mu\text{A}$	$V_{DS} = -50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.09	0.13	$\Omega$	$I_D = -4 \text{ A}$ $V_{GS} = -10 \text{ V}^{*1}$
		—	0.12	0.17	$\Omega$	$I_D = -4 \text{ A}$ $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	5.5	7.7	—	S	$I_D = -4 \text{ A}$ $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	1400	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	$C_{oss}$	—	720	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	220	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = -8 \text{ A}$
Rise time	$t_r$	—	120	—	ns	$V_{GS} = -10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	220	—	ns	$R_L = 3.75 \text{ }\Omega$
Fall time	$t_f$	—	160	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-1.05	—	V	$I_F = -8 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	190	—	$\mu\text{s}$	$I_F = -8 \text{ A}, V_{GS} = 0,$ $dI_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse Test





Hitachi Code	SP-12
JEDEC	—
EIAJ	—
Weight (reference value)	3.6 g

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